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FDN357N

N-Channel Enhancement Mode MOSFET

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Features

- V_{DS} = 30V,I_D = 2A
  $R_{DS(ON)}$ < 90mΩ @ V_{GS}=10V
  $R_{DS(ON)}$ < 100mΩ @ V_{GS}=4.5V

Typical Applications

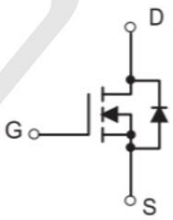
- Load switch
- PWM application

Shipping Quantity

- 3000pcs / Tape & Reel

SOT23

Circuit Diagram



N-MOS

Marking: 357N

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	2	A
Drain Current-Pulsed (Note 1)	I_{DM}	10	A
Maximum Power Dissipation	P_D	0.9	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

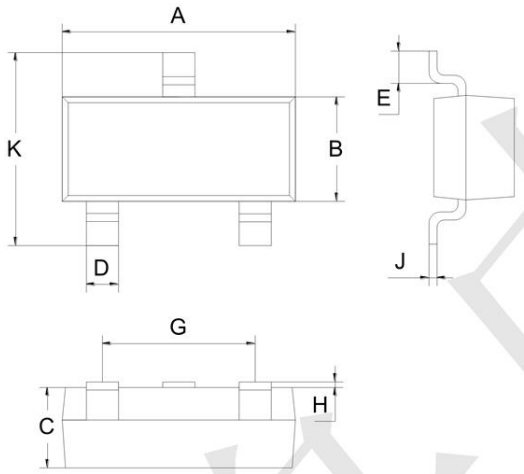
Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	138	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

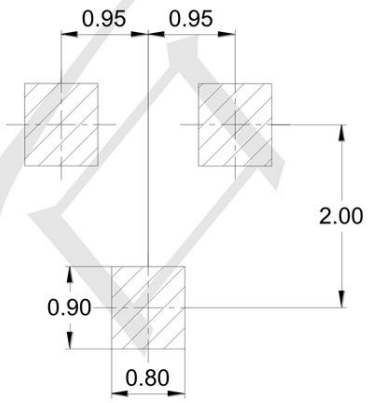
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1	1.5	3.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=2A	-	-	90	mΩ
		V_{GS}=4.5V, I_D=2 A	-	-	100	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=2A	14	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=10V,V_{GS}=0V, F=1.0MHz	-	235	-	PF
Output Capacitance	C_{oss}		-	35	-	PF
Reverse Transfer Capacitance	C_{rss}		-	18	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=15V,I_D=1A V_{GS}=10V,R_{GEN}=6Ω	-	3.5	-	nS
Turn-on Rise Time	t_r		-	1.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	17.5	-	nS
Turn-Off Fall Time	t_f		-	2.5	-	nS
Total Gate Charge	Q_g	V_{DS}=15V,I_D=2A,V_{GS}=10V	-	10	-	nC
Gate-Source Charge	Q_{gs}		-	0.95	-	nC
Gate-Drain Charge	Q_{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=2A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	2	A

Outline Drawing - SOT23



SOT-23		
Dimension	**Min.**	**Max.**
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60

Land Pattern - SOT23



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